

Please insert the following abstract on new page 14.

ABSTRACT OF THE DISCLOSURE

Disclosed is a method for manufacturing a diamond film of electronic quality at a high rate using a pulsed microwave plasma. The plasma that has a finite volume is formed near a substrate (in a vacuum chamber) by subjecting a gas containing at least hydrogen and carbon to a pulsed discharge. The pulsed discharge has a succession of low-power states and of high-power states, and a peak absorbed power P_c , in order to obtain carbon-containing radicals in the plasma. These carbon-containing radicals are deposited on the substrate in order to form a diamond film. Power is injected into the volume of the plasma with a peak power density of at least 100 W/cm^3 , while maintaining the substrate to a substrate temperature of between 700°C and 1000°C .